

028TSMC PVT 04

PVT Detector

OVERVIEW

028TSMC PVT 04 is а unique solution intended to continuously monitor IC status at several on-die locations. It is able to detect manufacturing deviation. process perform voltage and die temperature measurement. PVT Detector consists of VT module as a calculation center voltage and temperature for measurements, Process detector with process unit for standard-voltage, lowvoltage and high-voltage threshold MOS transistors and IO 2.5V transistor, voltage/temperature sensor units and voltage sensor units. VT module is able to maintain up to 32 external voltage and voltage/temperature sensor units of four types in any variations: for Core voltage measurement range from 0.1V to 1.15V, for IO voltage measurement range from 1.5V÷2.0V, for IO voltage



measurement range from 1.5V÷3.63V and additional 4.0V÷7.0V IO voltage measurement range. Process detector embeds VT sensor unit for Core voltage measurement and can be placed on the die in quantity up to 31 cells IP technology: TSMC 28nm eFlash.

IP status: pre-silicon verification.

Silicon area: VT module - 0.1151mm²; Process detector - 0.005016mm²; Sensor Units for 0.9V/1.8V/3.3V/5V temperature/voltage measurement -0.001514 mm²/0.001895 mm²/0.002795 mm²/0.003485 mm²; Sensor Units for 0.9V/1.8V/3.3V/5V voltage measurement - 0.000648mm²/ 0.001041mm²/ 0.001767mm²/ 0.002571mm².

ELECTRICAL CHARACIERISTICS												
Demomentary	Symbol	Conditions			I.I.a.:4a							
rarameter	Symbol			min	typ.	max	Units					
Core supply voltage	V _{DD09}	-			0.81	0.9	0.99	V				
IO supply voltage	V _{DD33}	-			2.97	3.3	3.63	V				
Operating temperature range	T_j	-			-40	27	150	°C				
Voltage measurement range	V _{MR09}	For 0.9V VT sensor unit			0.1	-	1.15	V				
	V _{MR18}	For 1.8V VT sensor unit			1.5	-	2.0	V				
	V _{MR33}	For 3.3V VT sensor unit			1.5	-	3.63	V				
	V _{MR5}	For 5.0V VT sensor unit			4	-	7	V				
Output DATA resolution	K	-			-	10	-	bit				
Clock frequency	F _{CLK}	-			-	32	-	kHz				
Current consumption	I _{CCVDD09_VT}	In case of V/T	@AVDI	D09	-	0.2	31	uA				
	I _{CCVDD33_VT}	measurement	@AVDI	D33	-	323	399					
	Iccvdd09_p	In case of Process	@AVDI	D09	-	200	250	11 4				
	I _{CCVDD33_P}	detection	@AVDD33 -		-	5	10	uA				
Shutdown current	I_{CCSTD_VDD09}	@AVDD09			-	0.1	2.31	uA				
	I _{STD_VDD33}	@AVDD33			-	0.1	0.97	uA				
Bandgap voltage	V_{BG}	-		796	805	815	mV					
Voltage measurement inaccuracy for 0.9V VT sensor unit	A_{V_MR09}	Without trimming δ 3δ		δ	-	-	0.6	%				
				3δ	-	-	2.0					
Voltage measurement inaccuracy for 1.8V VT sensor unit	Av_mr18	Without trimming $\frac{\delta}{3\delta}$		δ	-	-	0.6	%				
				3δ	-	-	1.9					
Voltage measurement inaccuracy for	A_{V_MR33}	Without trimming δ 3δ		δ	-	-	0.9	%				
3.3V VT sensor unit				3δ	-	-	2.9					

Ver. 1.0



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Danamatan	Symbol	Conditions		Value			Unita
rarameter				min	typ.	max	Units
Voltage measurement inaccuracy for 5.0V VT sensor	A_{V_MR5}	Without trimming	δ	-	-	0.8	- %
			3δ	-	-	2.9	
Temperature measurement range	T _{MR}	-		-40	-	150	°C
Temperature measurement accuracy	A _T	With out triggening	δ	-	-	2.2	°C
		without unninning	3δ	-	-	6.6	
		With trimming	δ	-	-	0.4	
			3δ	-	-	0.8	